



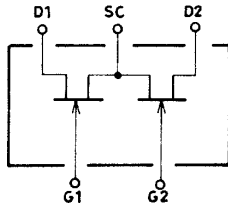
FC11

N-Channel Junction Silicon FET Low-Frequency General-Purpose Amp, Differential Amp Applications

Features

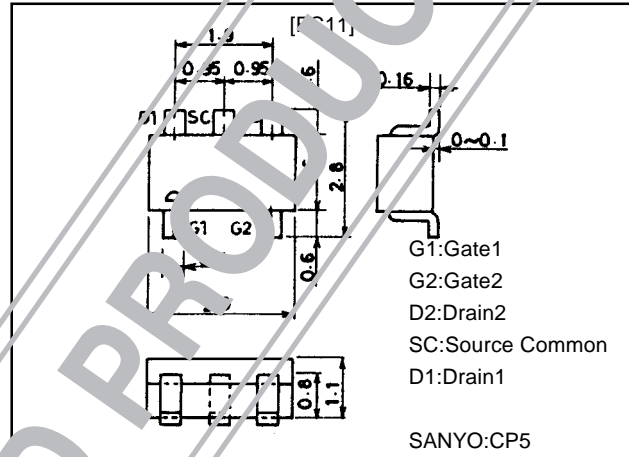
- Adoption of FBET process.
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC11 is formed with two chips, being equivalent to the 2SK771, placed in one package.
- Excellent in the thermal equilibrium and pair capability and suitable for use in differential amp.
- Common source.

Electrical Connection



Package Dimensions

unit:mm
2070



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSX}		40	V
Gate-to-Drain Voltage	V_{GD}		-40	V
Gate Current	I_G		10	mA
Drain Current	I_D		10	mA
Allowable Power Dissipation	$P_{D(allow)}$	unit	200	mW
Total Dissipation	P_T		300	mW
Junction Temperature	T_J		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Drain Breakdown Voltage	$V_{(BR)GDS}$	$I_G=10\mu A, V_{DS}=0$	-40			V
Gate Cutoff Current	I_{GSS}	$V_{GS}=-20V, V_{DS}=0V$			-1.0	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1\mu A$	-0.3	-0.9	-1.8	V
Gate-to-Source Voltage Temp	ΔV_{GS}	$ V_{GS \text{ large}} - V_{GS \text{ small}} , V_{DS}=10V, I_D=1mA$			30	mV
Drain Current	I_{DSS}	$V_{DS}=10V, V_{GS}=0V$	1.2*		6.0*	mA
Drain Current Ratio		$V_{DS}=10V, I_{DSS \text{ small}}/I_{DSS \text{ large}}$	0.9			
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, V_{GS}=0V, f=1kHz$	4.5	9.0		mS
Forward Transfer Admittance Ratio		$V_{DS}=10V, Y_{fs} _{\text{small}} / Y_{fs} _{\text{large}}$	0.9			
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$		9.0		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$		2.1		pF
Noise Figure	NF	$V_{DS}=10V, R_G=1k\Omega, I_D=1mA, f=1kHz$		1.5		dB

Note*:The FC11 is classified by I_{DSS} as follows (unit:mA)

1.2	D	3.0	2.5	E	6.0
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Marking:11

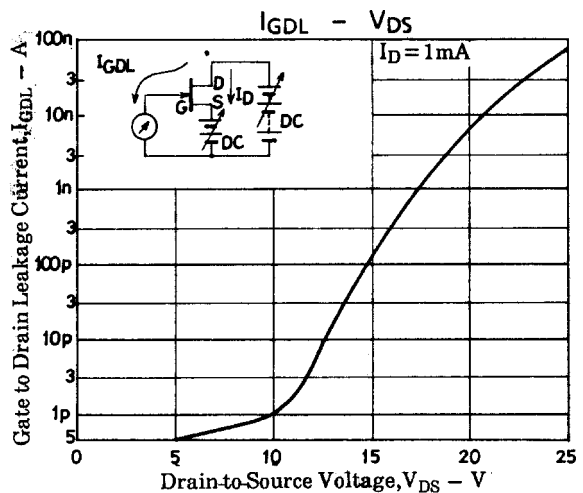
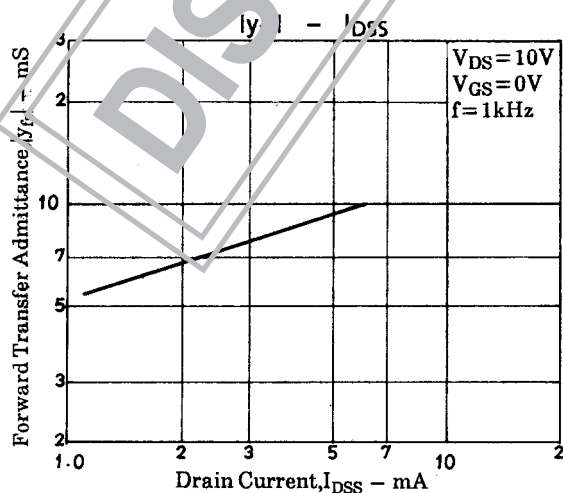
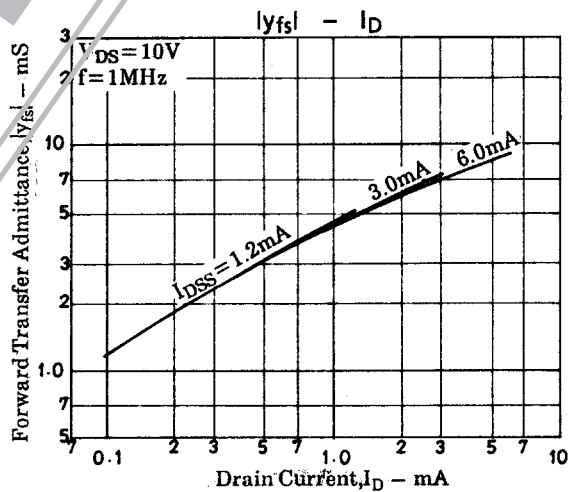
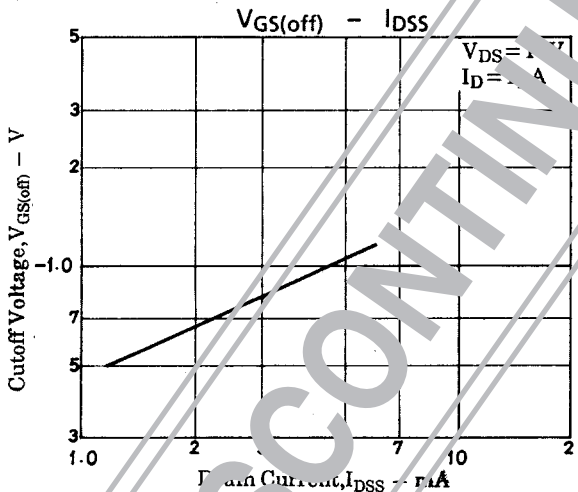
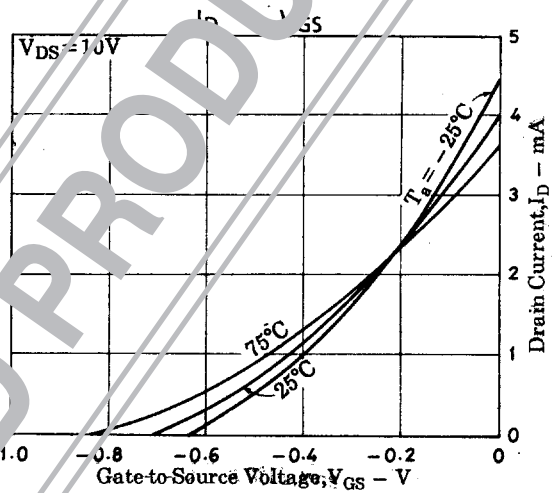
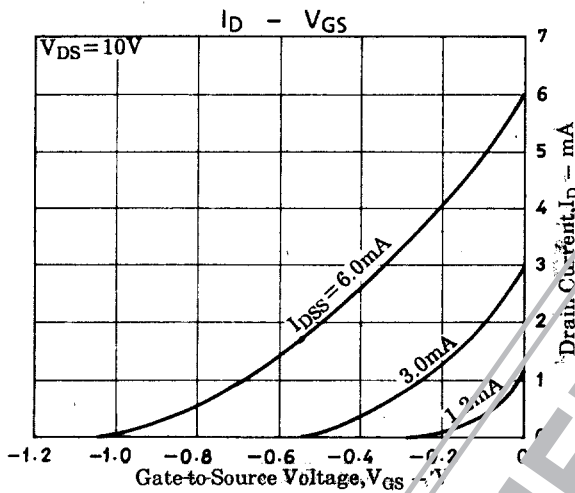
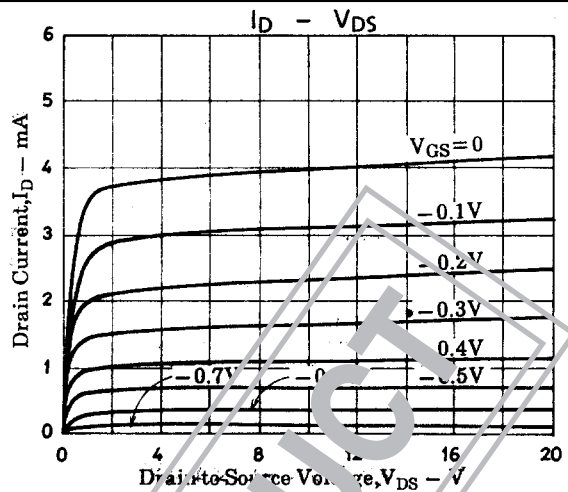
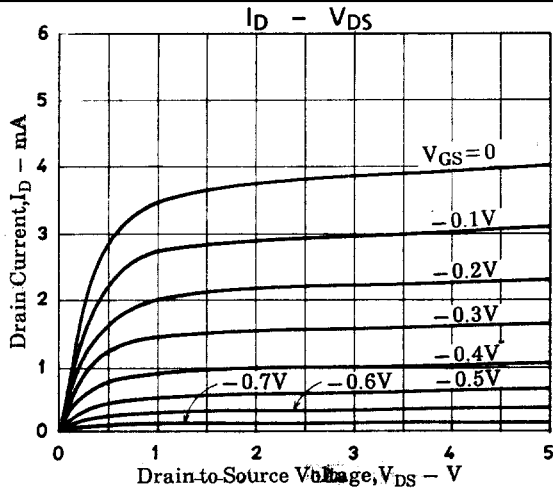
I_{DSS} rank:D,E

The Specifications shown above are for each individual transistor.

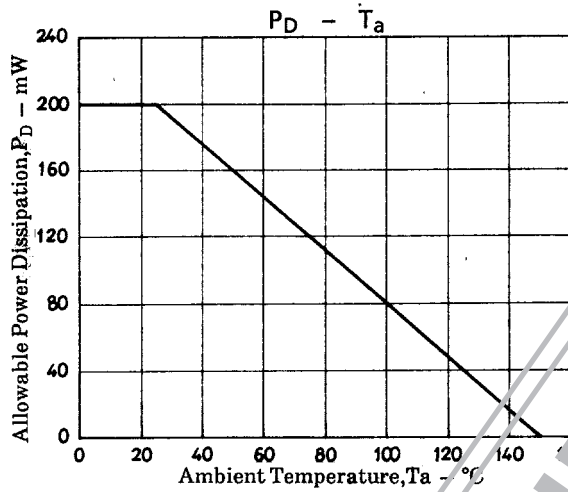
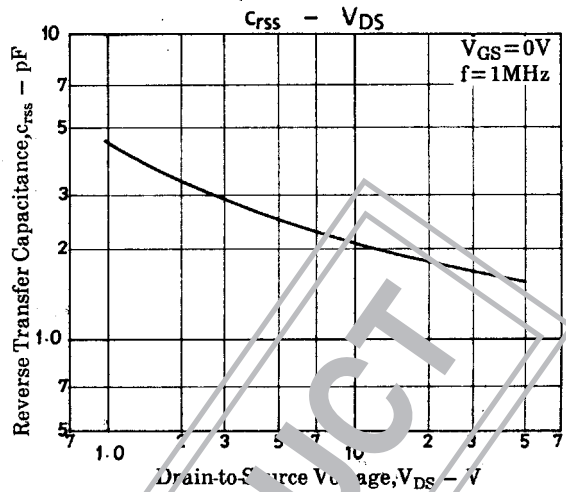
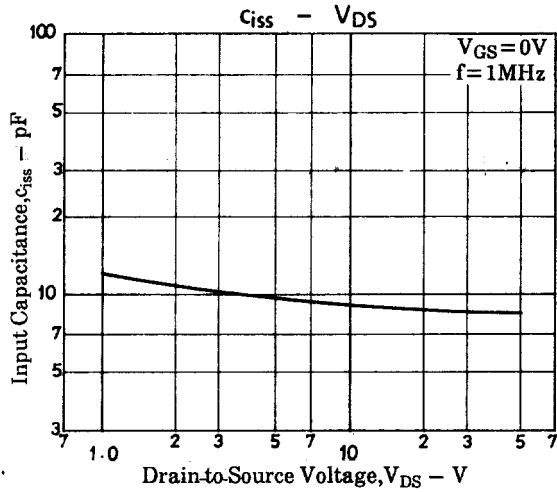
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